Amendments to the Specification:

Please replace paragraphs [0041] and [0063] with the following amended paragraphs:

[0041] A protective layer may be used to protect underlying layers during subsequent fabrication processes. For example, the processes used to fabricate metal or metal oxide top electrodes may damage organic layers, and a protective layer may be used to reduce or eliminate such damage. In device 100, protective layer 155 may reduce damage to underlying organic layers during the fabrication of cathode 160. Preferably, a protective layer has a high carrier mobility for the type of carrier that it transports (electrons in device 100), such that it does not significantly increase the operating voltage of device 100. CuPc, BCP, and various metal phthalocyanines are examples of materials that may be used in protective layers. Other materials or combinations of materials may be used. The thickness of protective layer 155 is preferably thick enough that there is little or no damage to underlying layers due to fabrication processes that occur after organic protective layer 160 is deposited, yet not so thick as to significantly increase the operating voltage of device 100. Protective layer 155 may be doped to increase its conductivity. For example, a CuPc or BCP protective layer 160 may be doped with Li. A more detailed description of protective layers may be found in U.S. Patent Published Application ~~Serial~~ No. ~~09/931,948~~US 2004-0174116 A1 to Lu et al., which is incorporated by reference in its entirety.

[0063] UPS measurements were carried out in a custom-designed UHV chamber (base pressure 1×10^{-10} Torr) interconnected with the OMBD growth chamber. Further details may be found in J. Xue and S. R. Forrest, J. Appl. Phys., 95, 1869 (2004). ~~xx, xxxx (2003) (in press).~~ Organic films were grown by OMBD on highly doped n-Si (100) substrates coated with 400-Å-thick in-situ deposited Ag layers. HeI emission ($h\nu$ = 21.22 eV) from a VG UPS/2 lamp obtained from Thermo VG Scientific, West Sussex, East Grinstead RH19 1UB, U.K., was used as the photon source, and the UPS spectra were recorded with a multichannel hemispherical VG CLAM4 electron energy analyzer (also from Thermo VG Scientific), with a pass energy of 2.5 eV. The sample was biased at –3 V with respect to the analyzer, to distinguish between the analyzer and sample cutoffs. The overall resolution of the UPS spectra is approximately 0.1 eV.